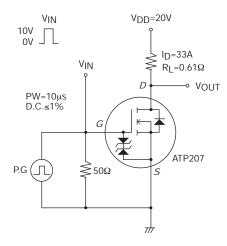
Electrical Characteristics at Ta=25°C

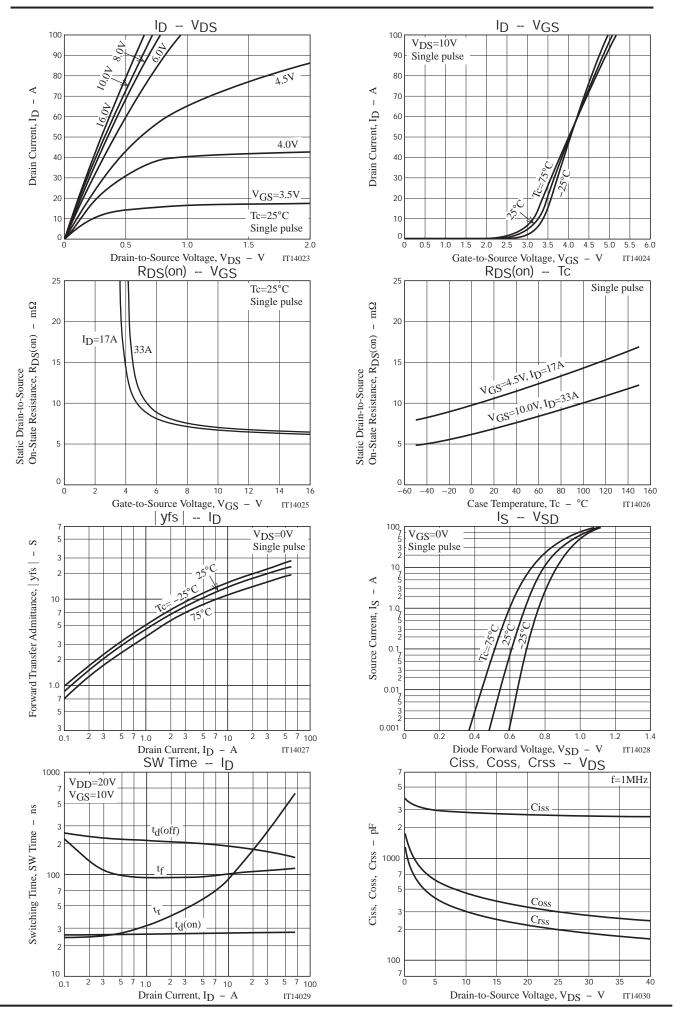
Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	40			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =40V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.5		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=33A	12	20		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =33A, V _G S=10V		7	9.1	mΩ
	R _{DS} (on)2	I _D =17A, V _G S=4.5V		11	15.5	mΩ
Input Capacitance	Ciss			2710		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		330		pF
Reverse Transfer Capacitance	Crss			220		pF
Turn-ON Delay Time	t _d (on)			27		ns
Rise Time	t _r	Sac appointed Toot Circuit		290		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		170		ns
Fall Time	tf			110		ns
Total Gate Charge	Qg			54		nC
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =65A		14		nC
Gate-to-Drain "Miller" Charge	Qgd			11		nC
Diode Forward Voltage	VSD	IS=65A, VGS=0V		1.0	1.2	V

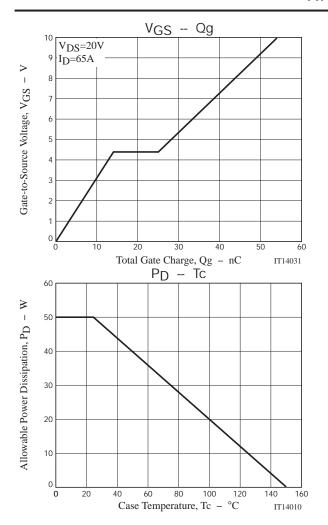
Switching Time Test Circuit

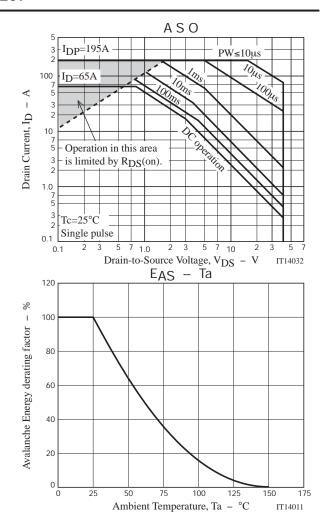


Ordering Information

Device Package		Shipping	memo	
ATP207-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free	





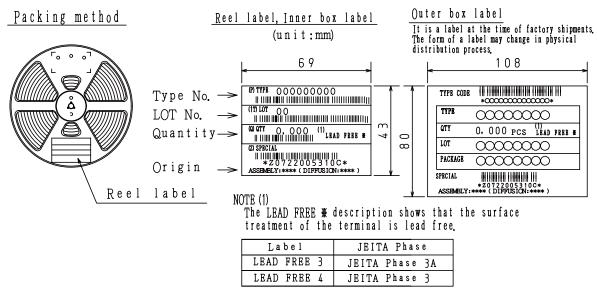


Taping Specification

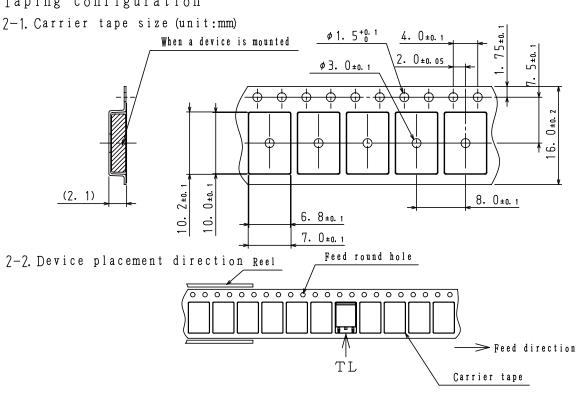
ATP207-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape	Carrier Tape Maximum Numbe				o r m a t
Lacrage Name	Туре	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
					1 reels contained	5 inner boxes contained
ATPAK	ATP	3,000	3,000	15,000	Dimensions:mm (external)	Dimensions:mm (external)
					340×340×28	355×355×165



7. Taping configuration

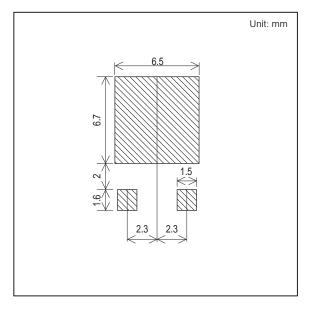


The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP207-TL-H

Land Pattern Example



Note on usage: Since the ATP207 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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